



N 沟道增强型场效应晶体管  
N-CHANNEL MOSFET

# JCS50N06H

## 主要参数 MAIN CHARACTERISTICS

ID	50 A
V <sub>DSS</sub>	60 V
R <sub>dson-max</sub> (@V <sub>GS</sub> =10V)	23 mΩ
Q <sub>G-typ</sub>	34 nC

## 用途

- 高频开关电源
- UPS 电源
- UPS

## APPLICATIONS

- High frequency switch mode power supplies
- UPS

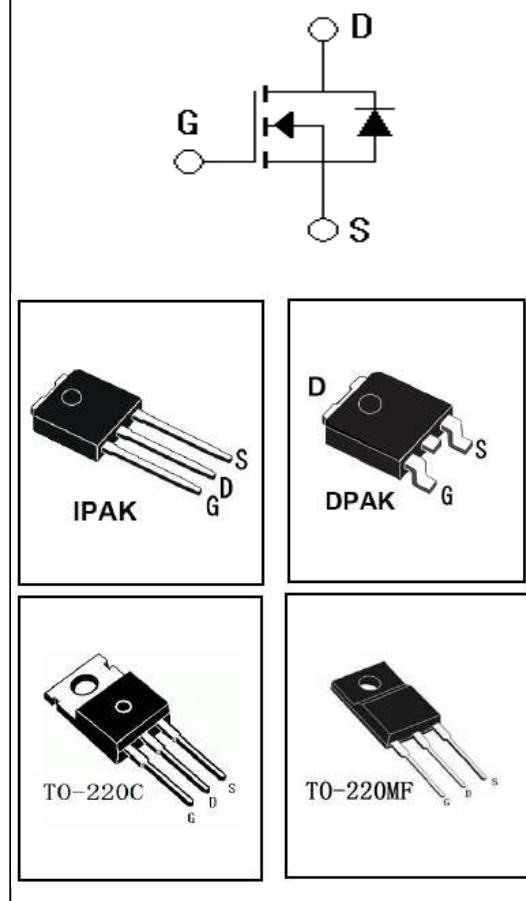
## 产品特性

- 低栅极电荷
- 低 C<sub>rss</sub>
- 开关速度快
- 产品全部经过雪崩测试
- 高抗 dv/dt 能力
- RoHS 产品

## FEATURES

- Low gate charge
- Low C<sub>rss</sub>
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHS product

## 封装 Package



## 订货信息 ORDER MESSAGE

订货型号 Order codes				印 记 Marking	封 装 Package
有卤-条管 Halogen-Tube	无卤-条管 Halogen-Free-Tube	有卤-编带 Halogen-Reel	无卤-编带 Halogen-Free-Reel		
JCS50N06VH-V-B	JCS50N06VH-V-BR	N/A	N/A	JCS50N06VH	IPAK
JCS50N06RH-R-B	JCS50N06RH-R-BR	JCS50N06RH-R-A	JCS50N06RH-R-AR	JCS50N06RH	DPAK
JCS50N06CH-C-B	JCS50N06CH-C-BR	N/A	N/A	JCS50N06CH	TO-220C
JCS50N06FH-F-B	JCS50N06FH-F-BR	N/A	N/A	JCS50N06FH	TO-220MF





JCS50N06H

## 绝对最大额定值 ABSOLUTE RATINGS (Tc=25°C)

项 目 Parameter	符 号 Symbol	数 值 Value			单 位 Unit
		JCS50N06RH/VH	JCS50N06CH	JCS50N06FH	
最高漏极—源极直流电压 Drain-Source Voltage	V <sub>DSS</sub>	60			V
连续漏极电流 Drain Current -continuous	I <sub>D</sub> T=25°C T=100°C	50		50*	A
		31.7		31.7*	A
最大脉冲漏极电流(注 1) Drain Current – pulse (note 1)	I <sub>DM</sub>	200*			A
最高栅源电压 Gate-Source Voltage	V <sub>GSS</sub>	±20			V
单脉冲雪崩能量(注 2) Single Pulsed Avalanche Energy (note 2)	E <sub>AS</sub>	500			mJ
雪崩电流(注 1) Avalanche Current (note 1)	I <sub>AR</sub>	50			A
重复雪崩能量 (注 1) Repetitive Avalanche Energy (note 1)	E <sub>AR</sub>	8.75	10.3	5.6	mJ
二极管反向恢复最大电压变化速率 (注 3) Peak Diode Recovery dv/dt (note 3)	dv/dt	7.0			V/ns
耗散功率 Power Dissipation	P <sub>D</sub> T <sub>c</sub> =25°C -Derate above 25°C	87.5	103.8	56	W
		0.70	0.83	0.45	W/°C
最高结温及存储温度 Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55~+150			°C
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T <sub>L</sub>	300			°C

\*漏极电流由最高结温限制

\*Drain current limited by maximum junction temperature



吉林华微电子股份有限公司

JILIN SINO-MICROELECTRONICS CO., LTD.



JCS50N06H

## 电特性 ELECTRICAL CHARACTERISTICS

项目 Parameter	符号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单位 Units
<b>关态特性 Off -Characteristics</b>						
漏一源击穿电压 Drain-Source Voltage	$V_{DSS}$	$I_D=250\mu A, V_{GS}=0V$	60	-	-	V
击穿电压温度特性 Breakdown Voltage Temperature Coefficient	$\Delta V_{DSS}/\Delta T_J$	$I_D=250\mu A$ , referenced to $25^\circ C$	-	0.6	-	V/ $^\circ C$
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=60V, V_{GS}=0V, T_C=25^\circ C$	-	-	1	$\mu A$
		$V_{DS}=48V, T_C=125^\circ C$	-	-	10	$\mu A$
正向栅极体漏电流 Gate-body leakage current, forward	$I_{GSSF}$	$V_{DS}=0V, V_{GS}=30V$	-	-	100	nA
反向栅极体漏电流 Gate-body leakage current, reverse	$I_{GSSR}$	$V_{DS}=0V, V_{GS}=-30V$	-	-	-100	nA
<b>通态特性 On-Characteristics</b>						
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D=250\mu A$	2.0	-	4.0	V
静态导通电阻 Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=25A$	-	19	23	$m\Omega$
正向跨导 Forward Transconductance	$g_{fs}$	$V_{DS}=30V, I_D=25A$ (note 4)	-	30	-	S
<b>动态特性 Dynamic Characteristics</b>						
输入电容 Input capacitance	$C_{iss}$	$V_{DS}=25V, V_{GS}=0V, f=1.0MHz$	-	900	1125	pF
输出电容 Output capacitance	$C_{oss}$		-	430	540	pF
反向传输电容 Reverse transfer capacitance	$C_{rss}$		-	80	100	pF





## 电特性 ELECTRICAL CHARACTERISTICS

开关特性 Switching Characteristics							
延迟时间 Turn-On delay time	$t_{d(on)}$	$V_{DD}=30V, I_D=50A, R_G=50\Omega$ $V_{GS} = 10V$ (note 4, 5)	-	40	90	ns	
上升时间 Turn-On rise time	$t_r$		-	100	210	ns	
延迟时间 Turn-Off delay time	$t_{d(off)}$		-	90	190	ns	
下降时间 Turn-Off Fall time	$t_f$		-	80	170	ns	
栅极电荷总量 Total Gate Charge	$Q_g$	$V_{DS} = 48V$ , $I_D = 50A$ $V_{GS} = 10V$ (note 4, 5)	-	34	45	nC	
栅一源电荷 Gate-Source charge	$Q_{gs}$		-	7	-	nC	
栅一漏电荷 Gate-Drain charge	$Q_{gd}$		-	17	-	nC	
漏一源二极管特性及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings							
正向最大连续电流	$I_S$			-	-	50 A	
Maximum Continuous Drain-Source Diode Forward Current	$I_S$			-	-	50 A	
正向最大脉冲电流	$I_{SM}$			-	-	200 A	
Maximum Pulsed Drain-Source Diode Forward Current	$I_{SM}$			-	-	200 A	
正向压降	$V_{SD}$	$V_{GS}=0V, I_S=50A$	-	1.4	V		
Drain-Source Diode Forward Voltage							
反向恢复时间	$t_{rr}$	$V_{GS}=0V, I_S=50A$	-	50	-	ns	
Reverse recovery time	$t_{rr}$						
反向恢复电荷	$Q_{rr}$	$dI_F/dt=100A/\mu s$ (note 4)	-	80	-	nC	
Reverse recovery charge							

## 热特性 THERMAL CHARACTERISTIC

项 目 Parameter	符 号 Symbol	最大 Max			单 位 Unit
		JCS50N06RH/VH	JCS50N06CH	JCS50N06FH	
结到管壳的热阻 Thermal Resistance, Junction to Case	$R_{th(j-c)}$	1.43	1.20	2.22	°C/W
结到环境的热阻 Thermal Resistance, Junction to Ambient	$R_{th(j-A)}$	62.5			°C/W

注释:

- 1: 脉冲宽度由最高结温限制
- 2:  $L=0.4mH, I_{AS}=50A, V_{DD}=25V, R_G=25 \Omega$ , 起始  
结温  $T_J=25^\circ C$
- 3:  $I_{SD} \leq 50A, di/dt \leq 300A/\mu s, VDD \leq BV_{DSS}$ , 起始结温  
 $T_J=25^\circ C$
- 4: 脉冲测试: 脉冲宽度  $\leq 300\mu s$ , 占空比  $\leq 2\%$
- 5: 基本与工作温度无关

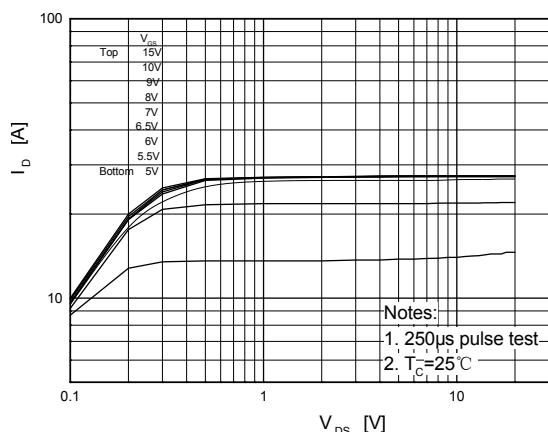
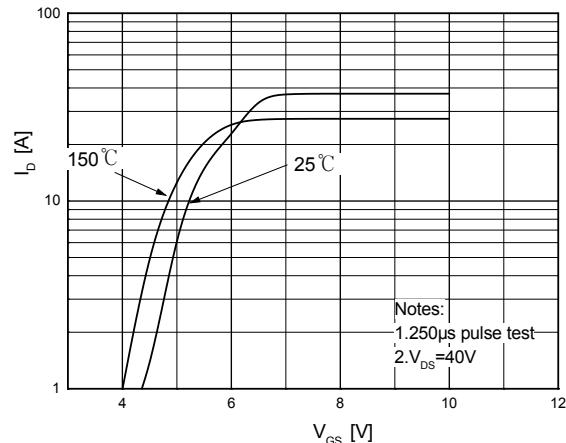
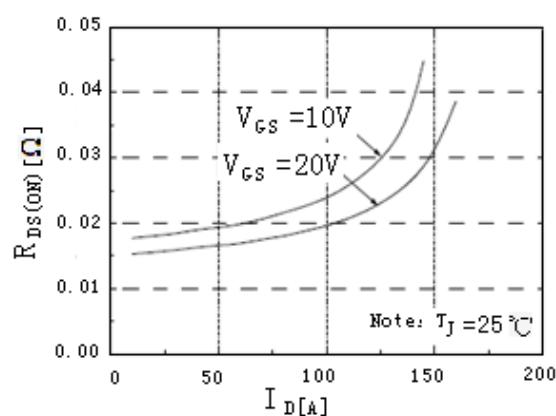
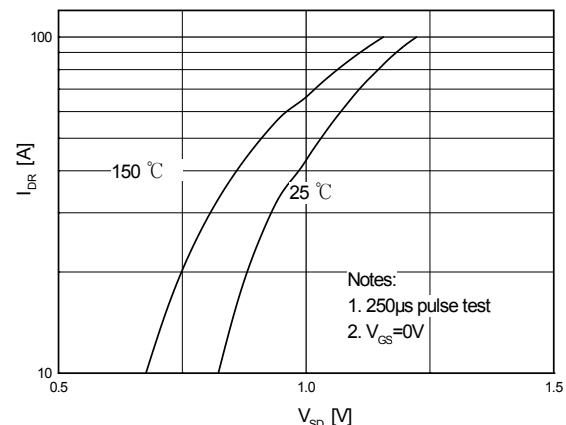
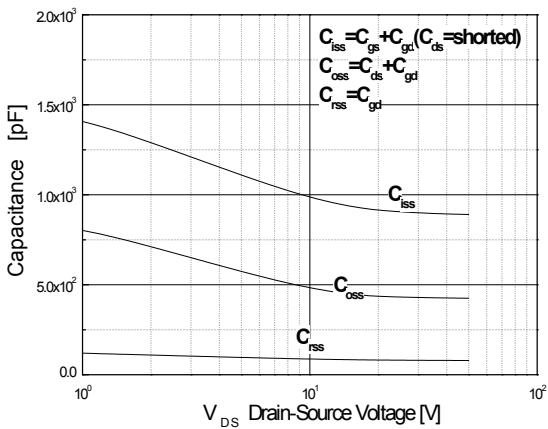
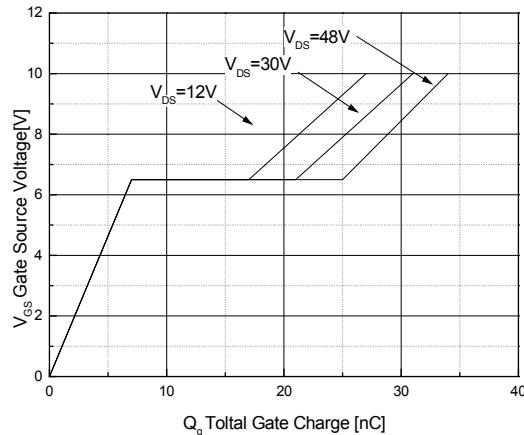
Notes:

- 1: Pulse width limited by maximum junction temperature
- 2:  $L=0.4mH, I_{AS}=50A, V_{DD}=25V, R_G=25 \Omega$ , Starting  
 $T_J=25^\circ C$
- 3:  $I_{SD} \leq 50A, di/dt \leq 300A/\mu s, VDD \leq BV_{DSS}$ , Starting  
 $T_J=25^\circ C$
- 4: Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$
- 5: Essentially independent of operating temperature



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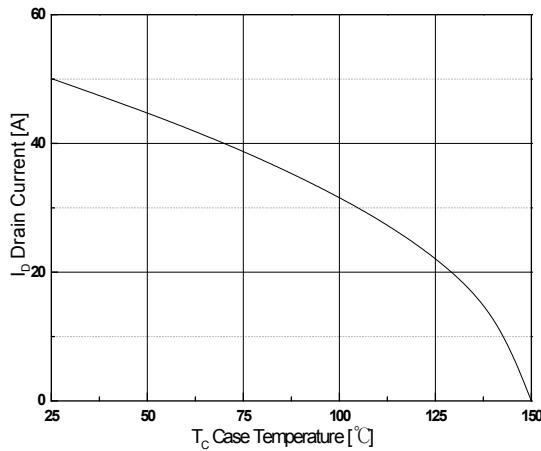
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**特征曲线 ELECTRICAL CHARACTERISTICS (curves)**
**On-Region Characteristics**

**Transfer Characteristics**

**On-Resistance Variation vs. Drain Current and Gate Voltage**

**Body Diode Forward Voltage Variation vs. Source Current and Temperature**

**Capacitance Characteristics**

**Gate Charge Characteristics**


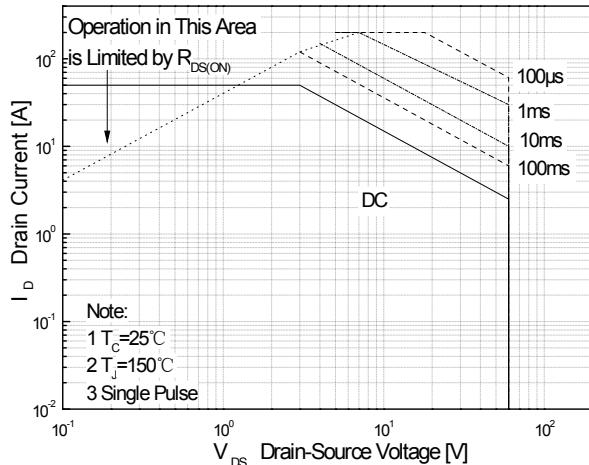


## 特征曲线 ELECTRICAL CHARACTERISTICS (curves)

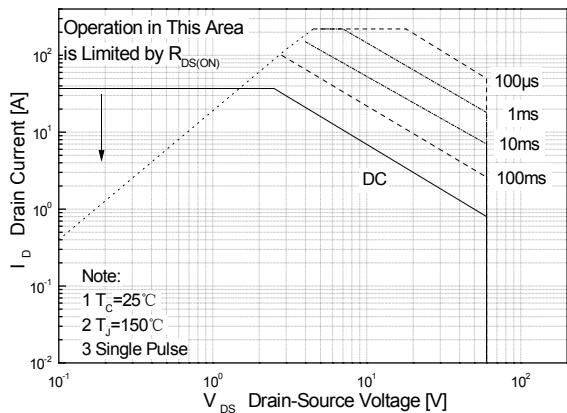
Maximum Drain Current vs. Case Temperature



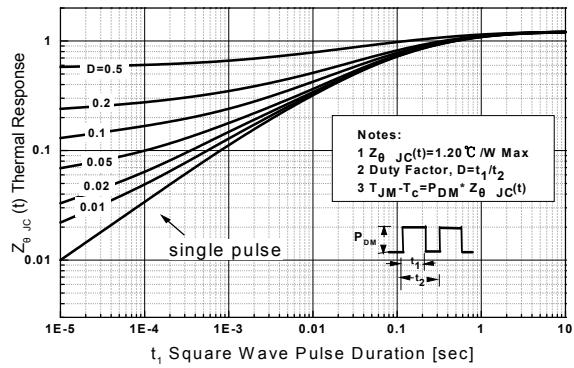
Maximum Safe Operating Area JCS50N06CH/RH/VH



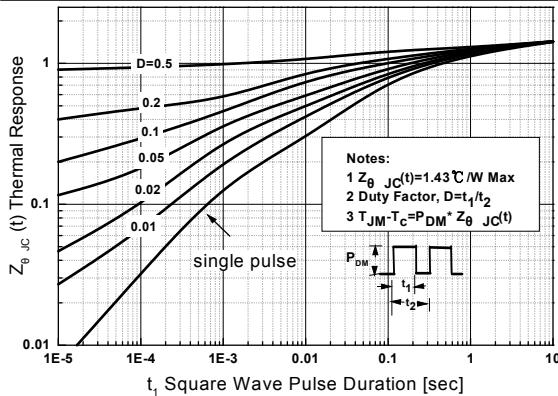
Maximum Safe Operating Area JCS50N06FH



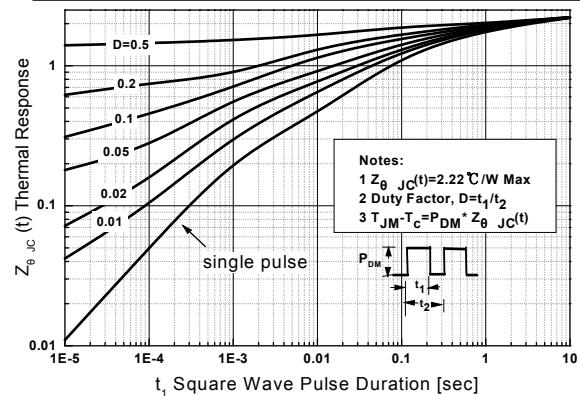
Transient Thermal Response Curve JCS50N06CH



Transient Thermal Response Curve JCS50N06VH/RH



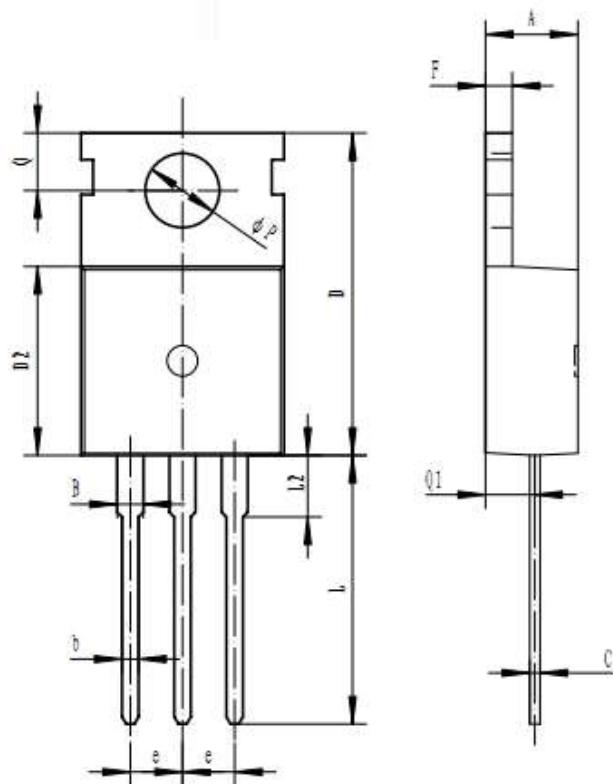
Transient Thermal Response Curve JCS50N06FH



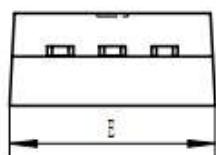
## 外形尺寸 PACKAGE MECHANICAL DATA

TO-220C

单位 Unit: mm



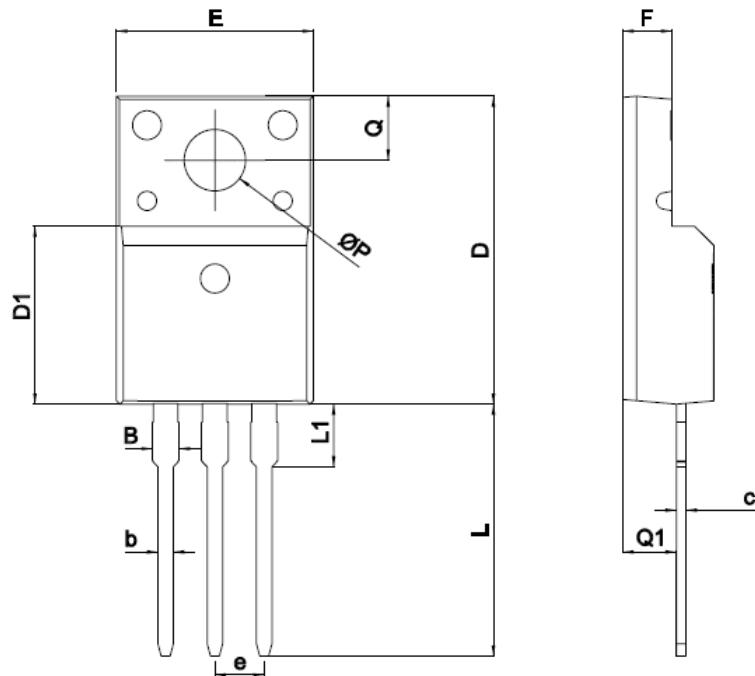
符号 symbol	MIN	MAX
A	4.30	4.70
B	1.22	1.40
b	0.70	0.95
c	0.40	0.65
D	15.20	16.20
D1	9.00	9.40
E	9.70	10.10
e	2.39	2.69
F	1.25	1.40
L	12.60	13.60
L1	2.80	3.20
Q	2.60	3.00
Q1	2.20	2.60
P	3.50	3.80



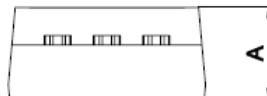
## 外形尺寸 PACKAGE MECHANICAL DATA

TO-220MF

单位 Unit: mm



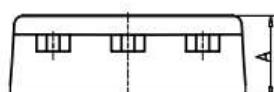
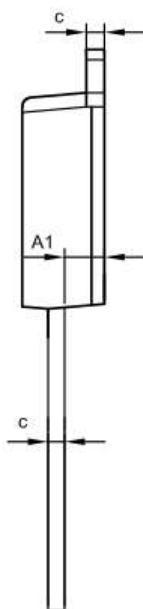
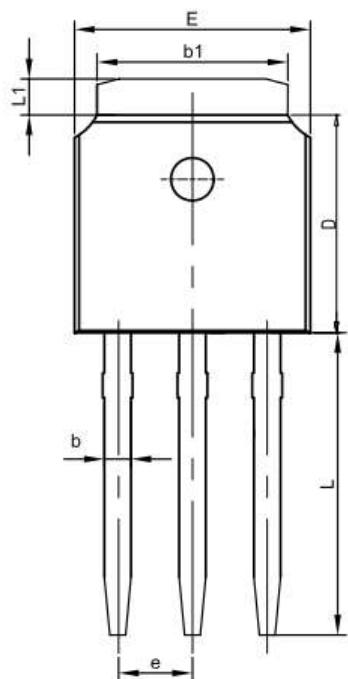
SYMBOL	mm	
	MIN	MAX
A	4.5	4.9
B		1.47
b	0.7	0.9
c	0.45	0.60
D	15.67	16.07
D1	9.04	9.20
e	2.54TYPE	
E	9.96	10.36
F	2.34	2.74
L	12.58	13.38
L1	3.13	3.33
Q	3.2	3.4
Q1	2.56	2.96
ΦP	3.08	3.28



## 外形尺寸 PACKAGE MECHANICAL DATA

I<sup>PAK</sup>

单位 Unit: mm



SYMBOL	MM	
	MIN	MAX
A	2.1	2.5
A1	0.87	1.27
b	0.63	0.93
b1	5.13	5.53
c	0.40	0.60
D	5.80	6.40
E	6.30	6.90
L	9.10	9.70
e	2.286BSC	
L1	0.82	1.22

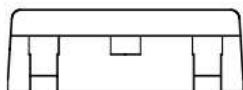
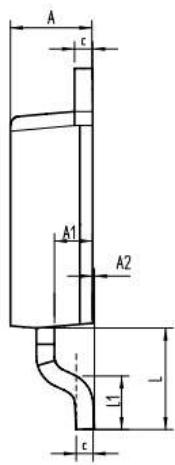
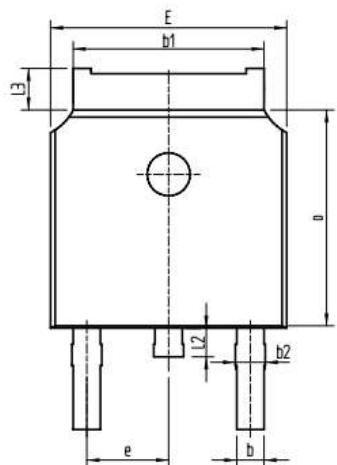


JCS50N06H

## 外形尺寸 PACKAGE MECHANICAL DATA

DPAK

单位 Unit: mm



SYMBOL	mm	
	MIN	MAX
A	2.16	2.41
A1	0.97	1.17
A2	0.00	0.15
b	0.63	0.93
b1	5.13	5.53
b2	0.66	0.96
c	0.40	0.60
D	5.80	6.40
E	6.30	6.90
e	2.286BSC	
L	2.50	3.30
L1	1.20	1.80
L2	0.60	1.00
L3	0.85	1.30



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3. 在电路设计时请不要超过器件的绝对最大额定值，否则会影响整机的可靠性。
4. 本说明书如有版本变更不另外告知

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2. We strongly recommend customers check carefully on the trademark when buying our product, if there is any question, please don't be hesitate to contact us.
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